



型号/TYPE: 4406

The 4406 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge.

This device is suitable for high side switch in SMPS and general purpose applications.

4406采用先进的沟道技术，以低栅极电荷提供优良的 $r_{d(on)}$ 。该装置适用于开关电源中的高压侧开关和通用场合。

主要特性/Features

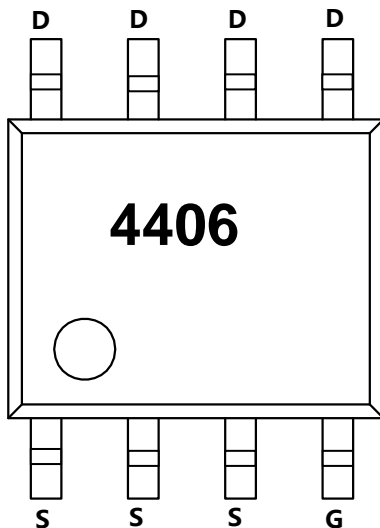
N-Channel Power MOSFET n沟道功率mosfet

应用/Application

High side switch in SMPS 开关电源高压侧开关

Load Switch 负荷开关

印字/MARKING 引脚定义/pin definition



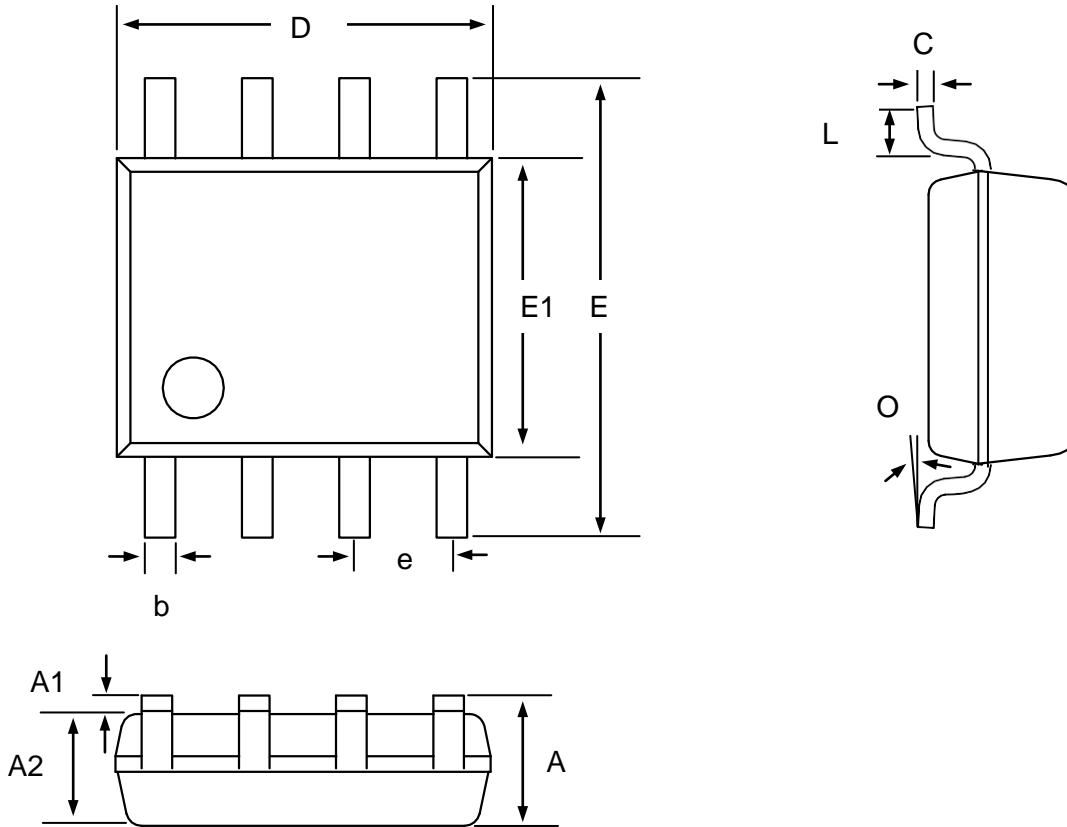


电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Description	Min.	Typ.	Max.	Test Conditions
V(BR)DSS	Drain-to-Source Breakdown Voltage	30V			V _{GS} = 0V, I _D = 250μ A
ID(Device Ref.)	Continuous Drain Current			60 A	T _J = 25°C
RDS(on)	Static Drain-to-Source On-Resistance		9mΩ	12mΩ	V _{GS} = 10V, I _D = 10A
			13mΩ	17mΩ	V _{GS} = 4.5V, I _D = 11.6A
VGS(th)	Gate Threshold Voltage	1.5 V	2 V	3V	V _{DS} = V _{GS} , I _D = 10mA
IDSS	Drain-to-Source Leakage Current			1μ A	V _{DS} = 30V, V _{GS} = 0V, T _J = 25°C
IGSS	Gate-to-Source Leakage Current			±100nA	V _{GS} = ±20V
T _J	Operating Junction and Storage Temperature Range	-55°C to 150°C Max.			
TSTG					



封装外观尺寸/SOP8 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	3.800	3.900	4.000
E1	0.400	0.835	1.2700
L	0°	4°	8°